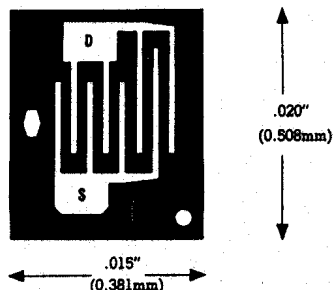


CHIP NUMBER

FN5.5



Die Size: 15 x 20 (mils)
0.381 x 0.508(mm)
3 x 4 (mils)
Pad Size: 0.076 x 0.102(mm)
GATE-SUBSTRATE

CONTACT METALLIZATION

Top Contact: > 12,000 Å Aluminum
Backside Contact: 3,000 Å Gold

ASSEMBLY RECOMMENDATIONS

It is advisable that:

- a) the die be eutectically mounted with gold silicon preform 98/2%.
- b) 1 mil (0.0254mm) aluminum wire be ultrasonically attached to the top contact.

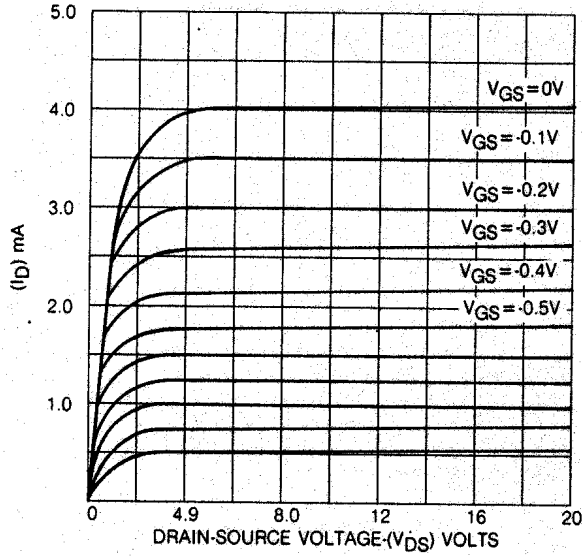
TYPICAL ELECTRICAL CHARACTERISTICS

PARAMETER	MIN.	TYP	MAX.	UNIT	TEST CONDITIONS
BVGSS	-40	-60	-80	V	V _{DS} = 0, I _G = 1μA
I _{DSS}	1.0	12	30	mA	V _{DS} = 20V, V _{GS} = 0
g _{fs}	1.0	4.0	6.0	mmho	V _{DS} = 20V, V _{GS} , = 0
I _{GSS}		-10	-100	pA	V _{GS} = -30V, V _{DS} = 0
r _{DS}	120	300	1000	Ω	V _{DS} = 100mV, V _{GS} = 0
V _{GS(off)}	-0.5	-3.0	-8.0	V	V _{DS} = 20V, I _D = 1nA
C _{rss}		1.8	3.0	pF	V _{DS} = 15V, I _D = 2mA, f = 1MHz
C _{iss}		6	8	pF	V _{DS} = 15V, I _D = 2mA, f = 1MHz
e _n		25	50	nV/√Hz	V _{DS} = 15V, I _D = 2mA, f = 10Hz

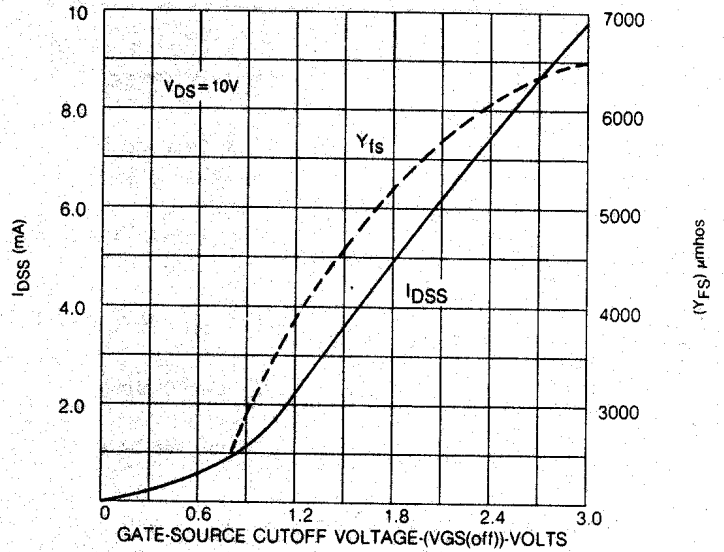
TYPICAL DEVICE TYPES: 2N5561 - 2N5563, UC210, UC220, 2N4221, 2N4222

CHIP TYPE FN5.5

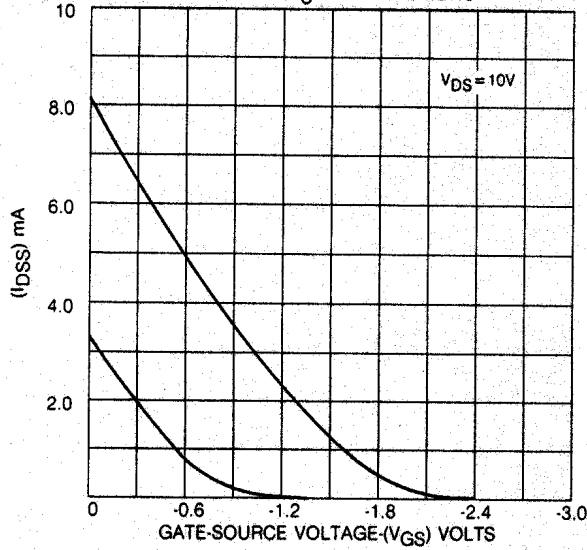
OUTPUT CHARACTERISTIC



FORWARD TRANSADMITTANCE VS GATE-SOURCE CUTOFF



TRANSFER V_S CHARACTERISTIC



FORWARD TRANSADMITTANCE

